

Features

- General Purpose, Low Cost
- Gain Bandwidth Product: 350KHz
- Low Quiescent Current: 17 μ A/Amplifier
- 0.01Hz-10Hz Noise: 1.5 μ VPP
- Zero Drift: 0.01 μ V/ $^{\circ}$ C (Typ)
- Input Bias Current: 20pA
- Unity Gain Stable
- Rail-to-Rail Input and Output
- Single or Dual Supply Operation
- Supply Voltage Range: 1.8V to 5.5V
- Operating Temperature: -50 $^{\circ}$ C ~ +125 $^{\circ}$ C
- Type Package:SOT23-5

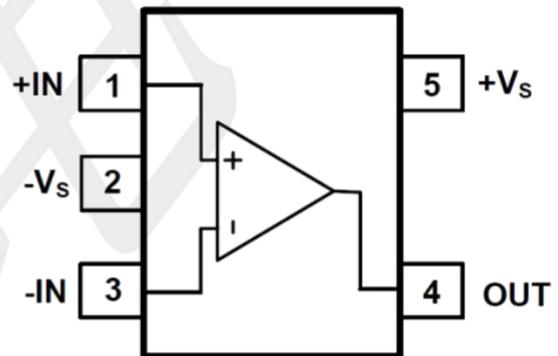
Applications

- Temperature Sensors
- Battery-Powered Instruments
- Smoke/Gas/Environment Sensors
- Medical Equipment
- Portable Instruments and Mobile Device
- Active Filters
- Piezo Electrical Transducer Amplifier
- Sensor Interface
- Handheld Test Equipment

General Description

The TLV333IDBVR of CMOS operational amplifiers use a proprietary auto-calibration technique to simultaneously provide very low offset voltage ($\pm 10\mu\text{V}$, maximum) and near-zero drift over time and temperature. These miniature, high-precision, low quiescent current (17 μA) amplifiers offer high impedance inputs that have a common-mode range 100 mV beyond the rails, and rail-to-rail output that swings within 50 mV of the rails. Single or dual supplies as low as 1.8 V (± 0.9 V) and up to 5.5 V (+2.75 V) can be used. These devices are optimized for low voltage, single-supply operation.

Pinout (top view)



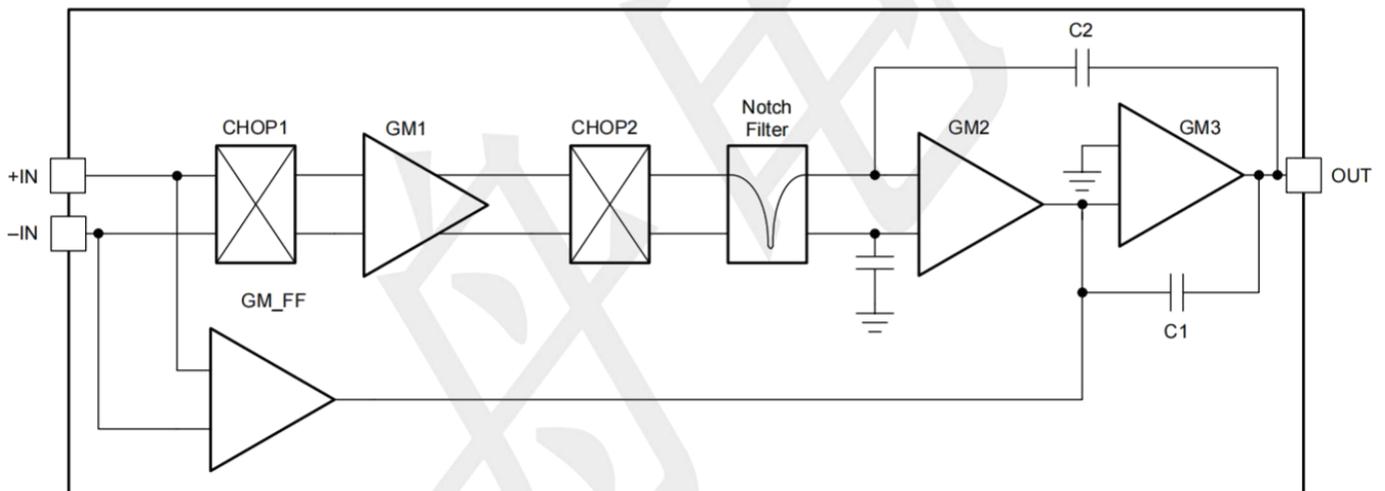
Pin Configurations

| Pin Number | Pin Name | Pin Function |
|------------|----------|-----------------------------------|
| 1 | +IN | In-phase input |
| 2 | -Vs | Chip Supply Voltage(Negative)/GND |
| 3 | -IN | Reverse input |
| 4 | OUT | Output |
| 5 | +Vs | Chip Supply Voltage(Positive)/VDD |

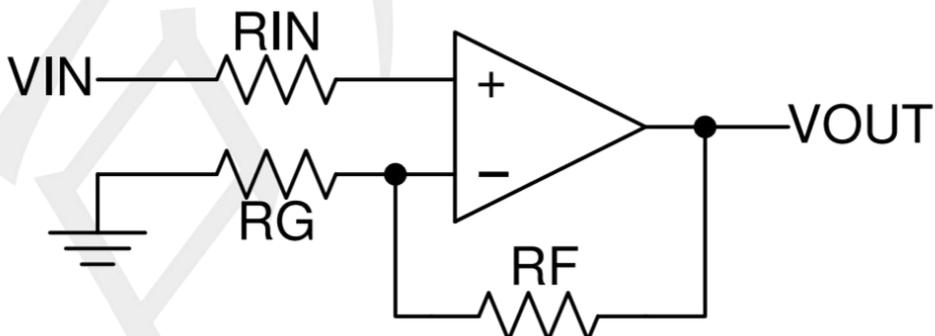
Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Condition | | Rating | UNIT |
|------------|---------------------------------------|-------------------|------|
| VDD to GND | Power Supply Voltage | 7V | V |
| IN+ or IN- | Signal Input Terminals Voltage | GND-0.3V~VDD+0.3V | V |
| IN+ or IN- | Signal Input Terminals Current | -1mA ~ +1mA | mA |
| OUT to GND | Output Short-Circuit | Continuous | mA |
| TJ | Junction Temperature | 150 | °C |
| LT | Lead Temperature (Soldering, 10 sec.) | 260 | °C |
| TA | Operating Temperature Range | -55 150 | °C |
| Tstg | Storage Temperature Range | -65 150 | °C |
| V(ESD) | Human body model (HBM) | ±4000 | V |
| V(ESD) | Charged-device model (CDM) | ±1000 | V |

BLOCK DIAGRAM



Power Supply Bypassing



Electrical Characteristics

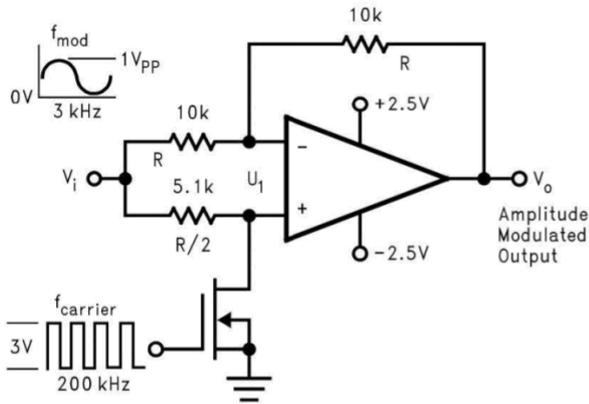
(At $T_A = +25^\circ\text{C}$, $V_S = +5\text{V}$, $V_{IN} = 0\text{V}$, unless otherwise noted.)

| PARAMETER | SYMBOL | TEST Conditions | MIN | TYP | MAX | UNIT |
|---------------------------------|-----------------|--|-----------|---------|--------------|------------------------------|
| Supply-Voltage Range | V_{DD} | Single-supply | 1.8 | -- | 5.5 | V |
| | | Dual-supply | ± 0.9 | -- | ± 2.75 | V |
| Quiescent Current/Amplifier | I_Q | $V_{DD} = 5\text{V}$ | -- | 17 | 28 | μA |
| Input Offset Voltage | V_{OS} | | -- | ± 1 | ± 15 | μV |
| Input Offset Voltage Tempco | dV_{OS}/dT | $T_A = -55^\circ\text{C}$ to 125°C | -- | 0.01 | -- | $\mu\text{V}/^\circ\text{C}$ |
| Input Bias Current | I_B | (2) | -- | 1 | 20 | PA |
| Input Bias Current | I_B | $T_A = -55^\circ\text{C}$ to 125°C | -- | -- | 180 | PA |
| Input Offset Current | I_{OS} | (2) | -- | 1 | 20 | PA |
| Common-Mode Voltage Range | V_{CM} | | GND-0.1 | -- | $V_{DD}+0.1$ | V |
| Common-Mode Rejection Ratio | CMRR | $\Delta V_{IN}=1\text{V}$ | 130 | 135 | -- | dB |
| Power-Supply Rejection Ratio | PSRR | $\Delta V_S=1\text{V}$ | -- | 135 | -- | dB |
| Open-Loop Voltage Gain | A_V | $\Delta V_{OUT}=1\text{V}$ | 140 | 150 | -- | dB |
| Output Swing from Positive Rail | $V_{OUT-SWING}$ | $R_L=10\text{k}\Omega$ | -- | 13 | -- | mV |
| Output Swing from Negative Rail | | $R_L=10\text{k}\Omega$ | -- | 17 | -- | mV |
| Capacitive Load Drive | $C_{L(3)}$ | $G = +1$, $V_{IN}=4\text{V}$ Step | -- | -- | 1 | nF |
| Output Short-Circuit Current | I_{SC} | Sinking or Sourcing | -- | 21 | -- | mA |
| Gain Bandwidth Product | GBW | | -- | 350 | -- | KHz |
| Slew Rate | SR | $G = +1$, $V_{IN}=4\text{V}$ Step | -- | 0.1 | -- | $\text{V}/\mu\text{s}$ |
| Input Voltage Noise | V_N | $f=0.1\text{Hz}$ to 10Hz | -- | 2 | -- | μV_{PP} |
| Input Voltage Noise PSD | | $f=1\text{kHz}$ | -- | 45 | -- | $\text{nV}/\sqrt{\text{Hz}}$ |
| Specified temperature | | | -50 | -- | 125 | $^\circ\text{C}$ |

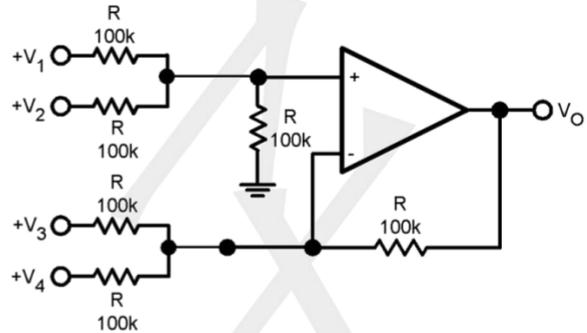
Notes:

- 1: All devices are 100% production tested at $T_A = +25^\circ\text{C}$; range is guaranteed by design, not production tested.
- 2: Parameter is guaranteed by design.
- 3: Capacitive load drive means that above a given maximum value, the output waveform will oscillate under the step response.

Typical Application Circuit

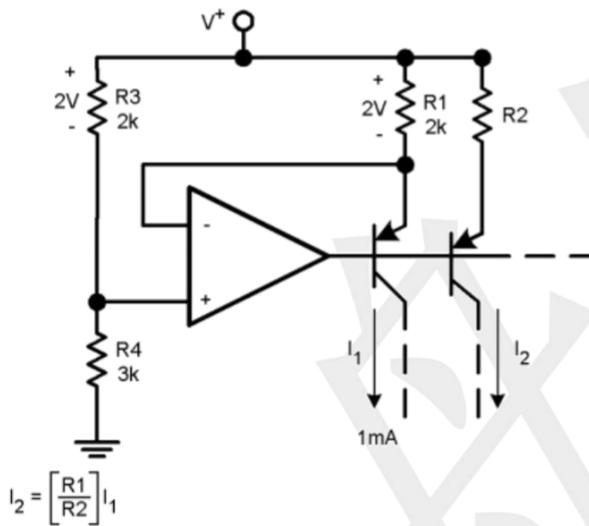


Amplitude modulator circuit

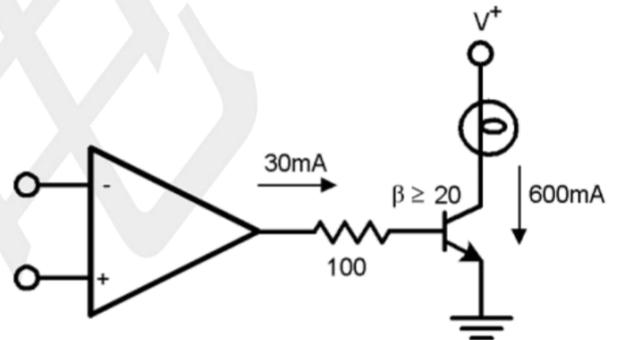


Note: $V_O = V_1 + V_2 - V_3 - V_4, (V_1 + V_2) \geq (V_3 + V_4)$ for $V_O \geq 0V_{DC}$

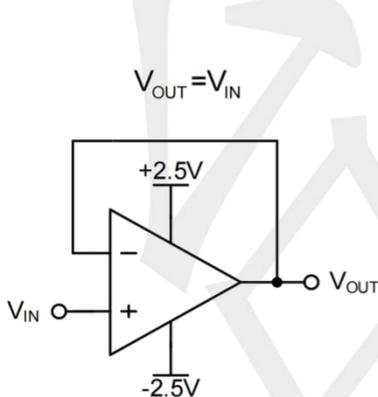
DC adder amplifier
($V_{IN'S} \geq 0V_{DC}, V_O \geq V_{DC}$)



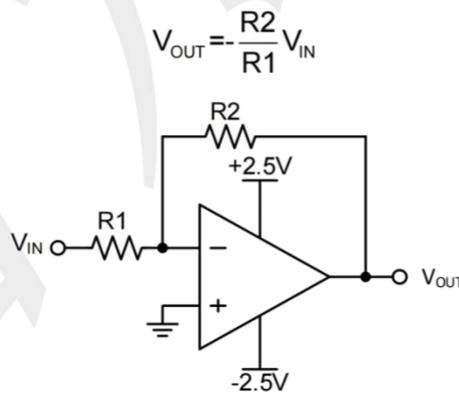
Fixed current source



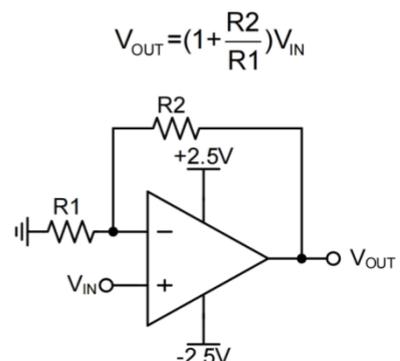
Lamp Driver



Voltage Follower

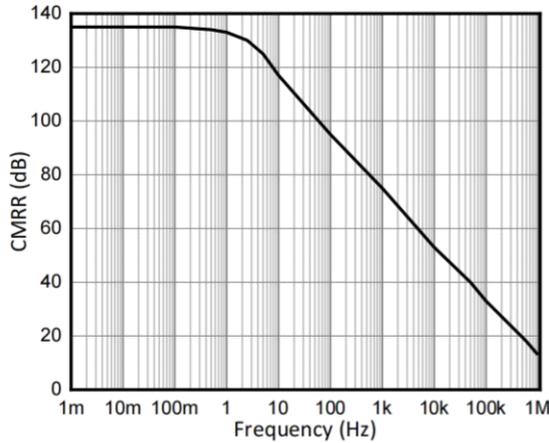


Inverting Proportional Amplifier

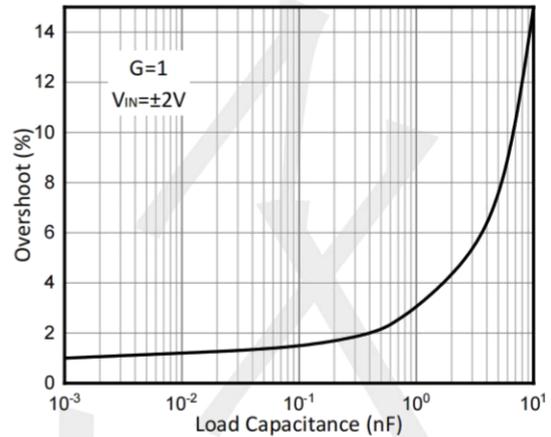


Noninverting Proportional Amplifier

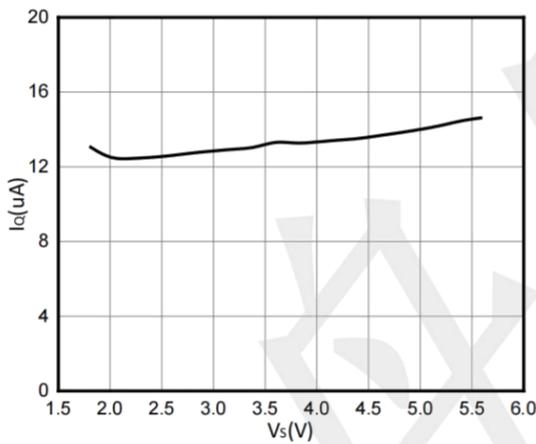
Typical Performance Characteristics (@TA = +25°C, unless otherwise specified.)



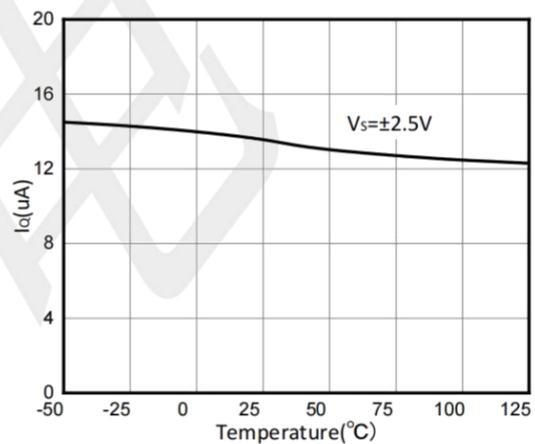
CMRR vs Frequency



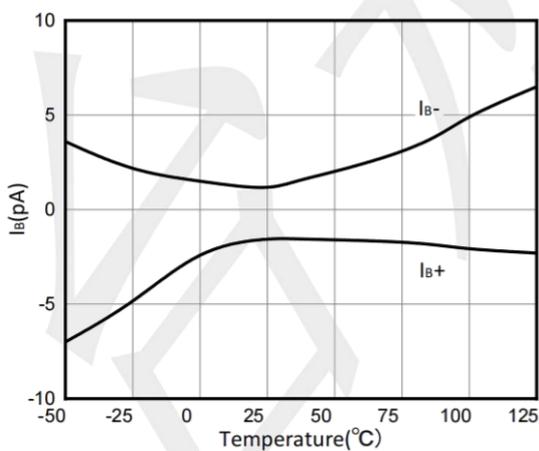
Large-Signal Overshoot vs Load Capacitance



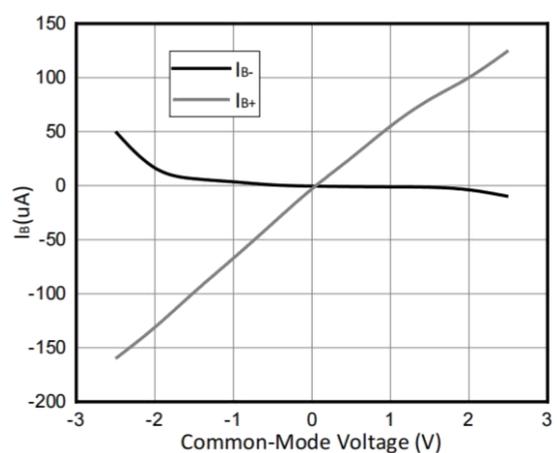
Quiescent Current vs Supply Voltage



Quiescent Current vs Temperature



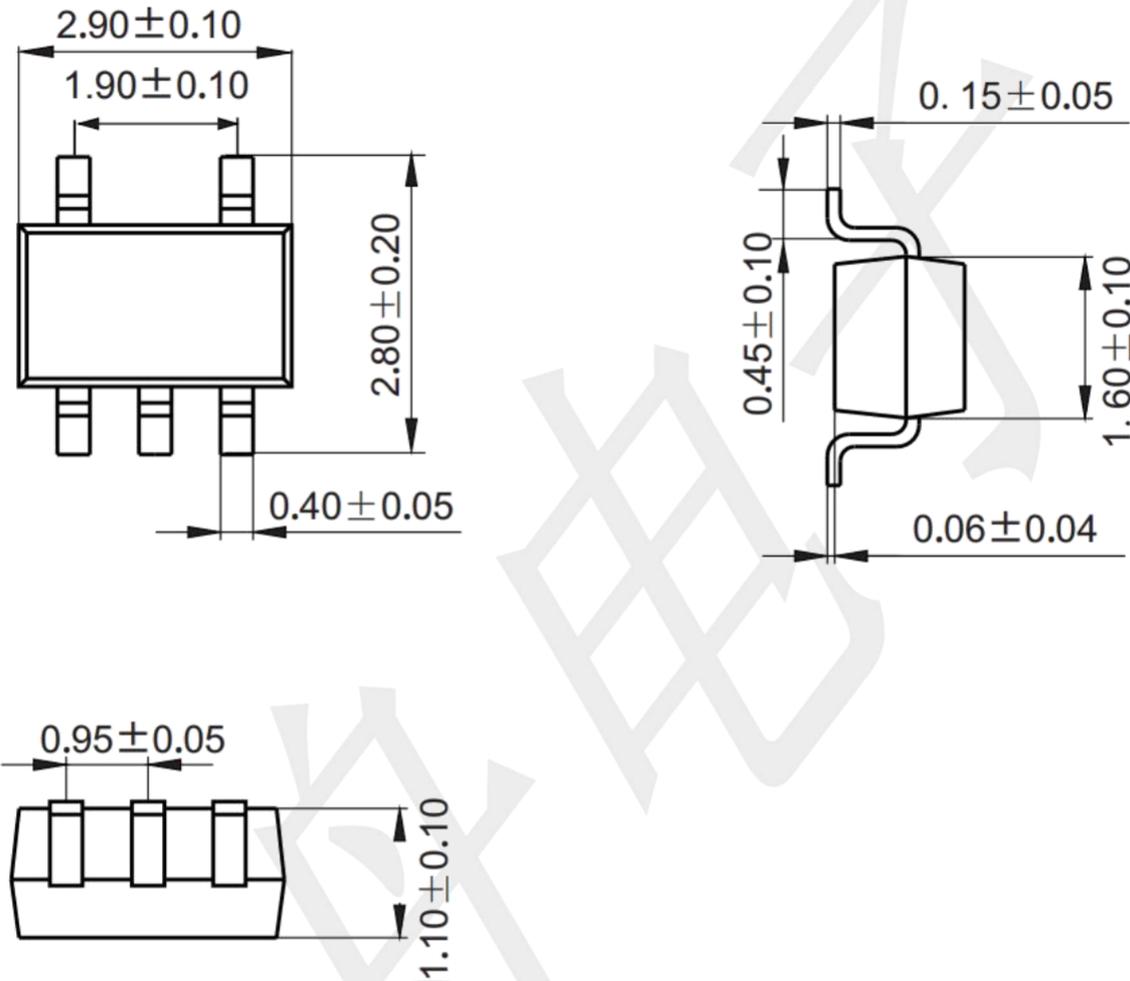
Input Bias Current vs Temperature



Input Bias Current vs Common-Mode Voltage

Package information (Unit: mm)

SOT23-5



Mounting Pad Layout (Unit: mm)

